

NPN RF Transistor

This device is designed for use as RF amplifiers, oscillators and multipliers with collector currents in the 1.0 mA to 30 mA range. Sourced from Process 43.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	15	V
V _{CBO}	Collector-Base Voltage	30	V
V _{EBO}	Emitter-Base Voltage	3.0	V
Ic	Collector Current - Continuous	50	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	N	Units	
		PN918	*MMBT918	
P _D	Total Device Dissipation	350	225	mW
	Derate above 25°C	2.8	1.8	mW/∘C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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NPN RF Transistor

(continued)

Electrical Characteristics	
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Electri	cal Characteristics TA = 25	S TA = 25°C unless otherwise noted			
Symbol	Parameter	Test Conditions	Min	Max	Units

OFF CHARACTERISTICS

V _{CEO(sus)}	Collector-Emitter Sustaining Voltage*	$I_{\rm C} = 3.0 \text{ mA}, I_{\rm B} = 0$	15		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{C} = 1.0 \ \mu A, \ I_{E} = 0$	30		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu {\rm A}, \ I_{\rm C} = 0$	3.0		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 15 \text{ V}, \text{ I}_{E} = 0$		0.01	μΑ
		V _{CB} = 15 V, T _A = 150°C		1.0	μA

ON CHARACTERISTICS

h _{FE}	DC Current Gain	I_{C} = 3.0 mA, V_{CE} = 1.0 V	20		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1.0 \text{ mA}$		0.4	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{\rm C} = 10$ mA, $I_{\rm B} = 1.0$ mA		1.0	V

SMALL SIGNAL CHARACTERISTICS

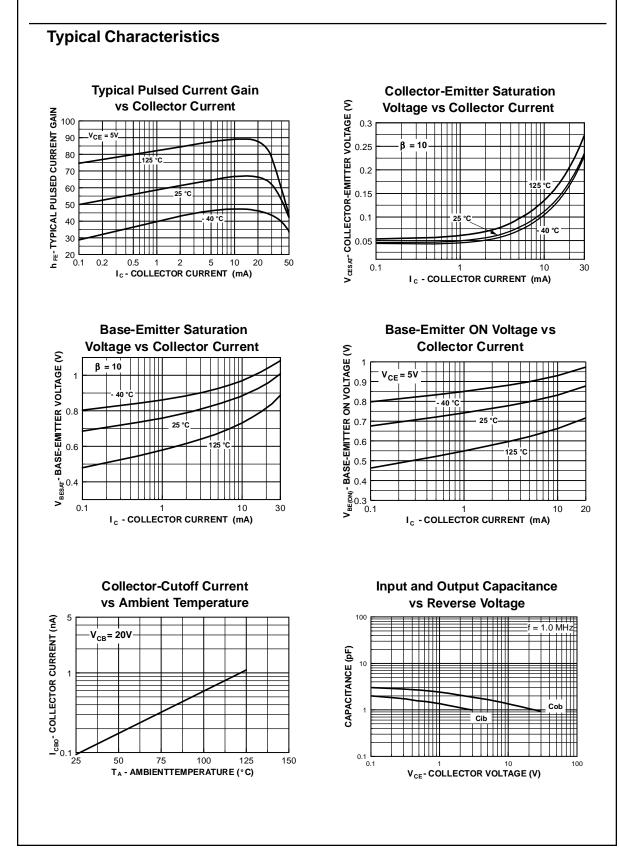
f _T	Current Gain - Bandwidth Product	$I_{C} = 4.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz	600		MHz
C _{obo}	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ $V_{CB} = 0, I_E = 0, f = 1.0 \text{ MHz}$		1.7 3.0	pF pF
C _{ibo}	Input Capacitance	$V_{BE} = 0.5 \text{ V}, I_{C} = 0, f = 1.0 \text{ MHz}$		2.0	pF
NF	Noise Figure	$I_{C} = 1.0 \text{ mA}, V_{CE} = 6.0 \text{ V}, R_{G} = 400\Omega, f = 60 \text{ MHz}$		6.0	dB

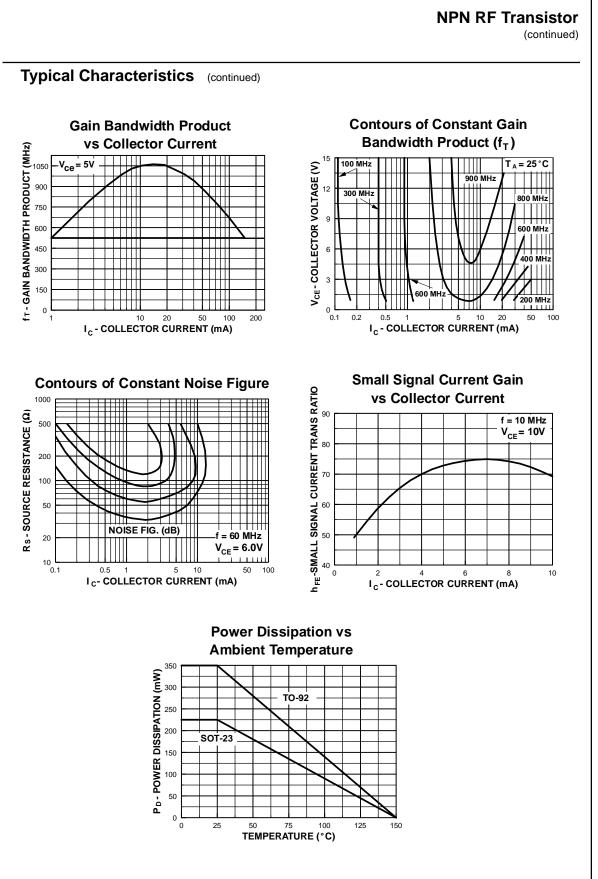
FUNCTIONAL TEST

G _{pe}	Amplifier Power Gain	$V_{CB} = 12 \text{ V}, \text{ I}_{C} = 6.0 \text{ mA},$ f = 200 MHz	15	dB
Po	Power Output	$V_{CB} = 15 \text{ V}, I_{C} = 8.0 \text{ mA},$ f = 500 MHz	30	mW
η	Collector Efficiency	$V_{CB} = 15 \text{ V}, \text{ I}_{C} = 8.0 \text{ mA},$ f = 500 MHz	25	%

*Pulse Test: Pulse Width \leq 300 $\mu s,$ Duty Cycle \leq 2.0%

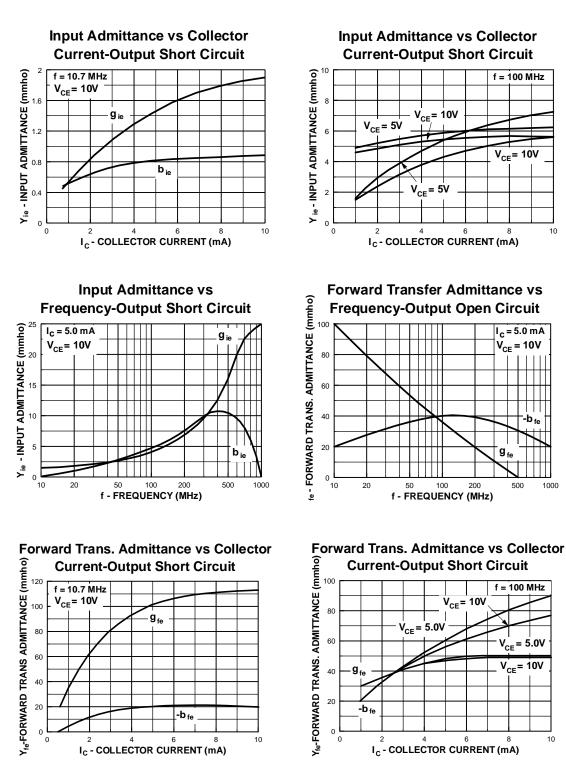
NPN RF Transistor (continued)











PN918 / MMBT918

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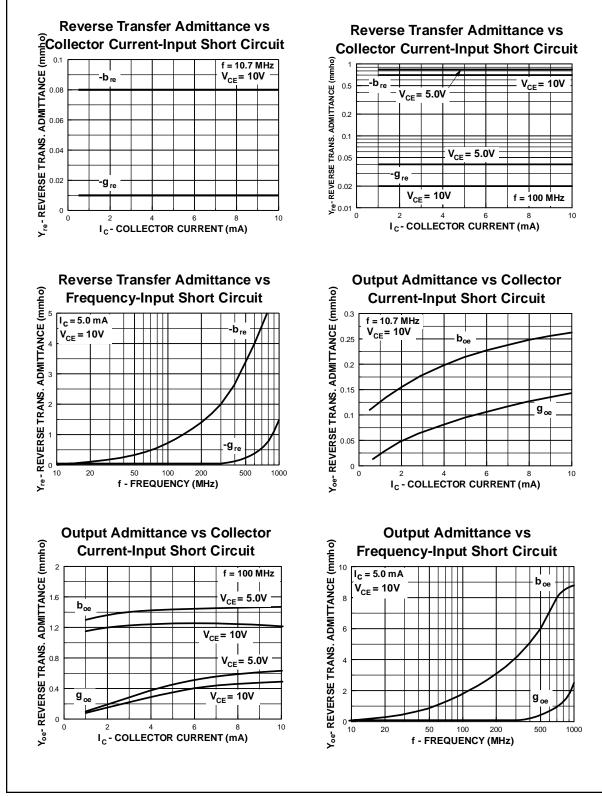
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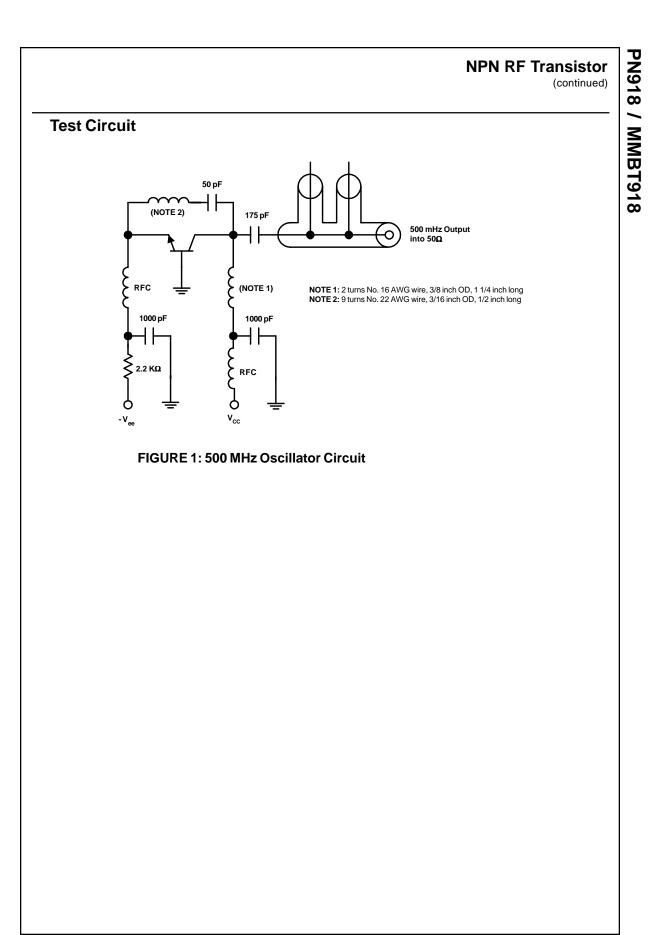
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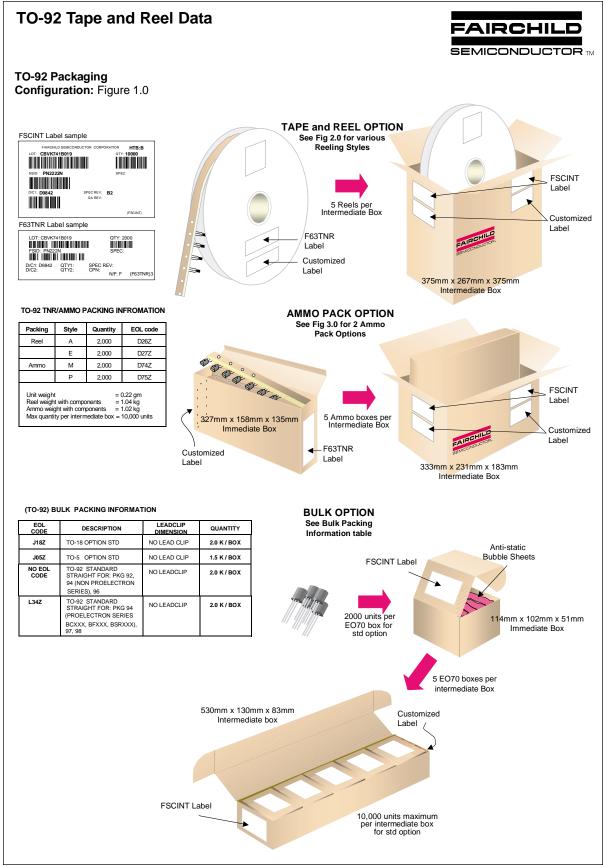
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NPN RF Transistor

Common Emitter Y Parameters vs. Frequency (continued)

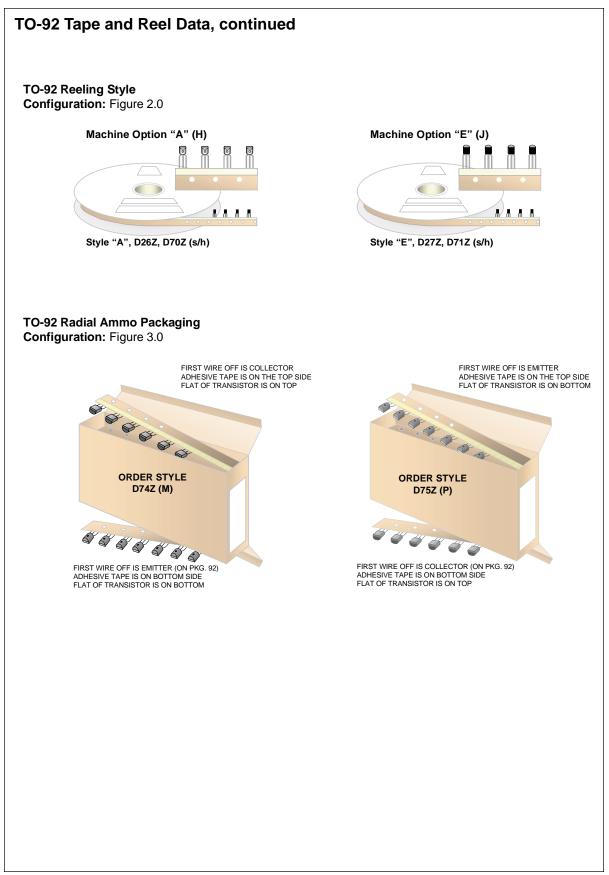




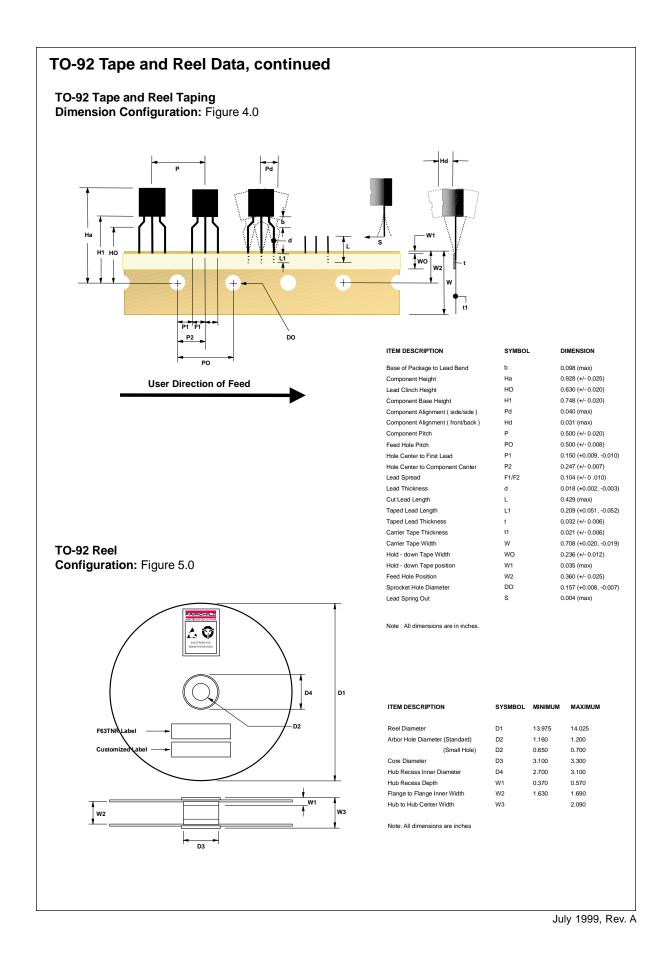


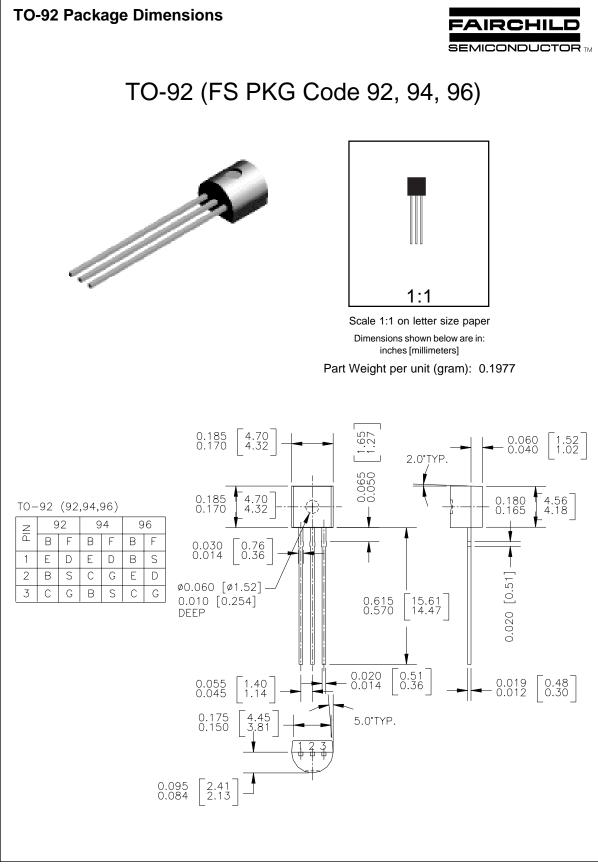
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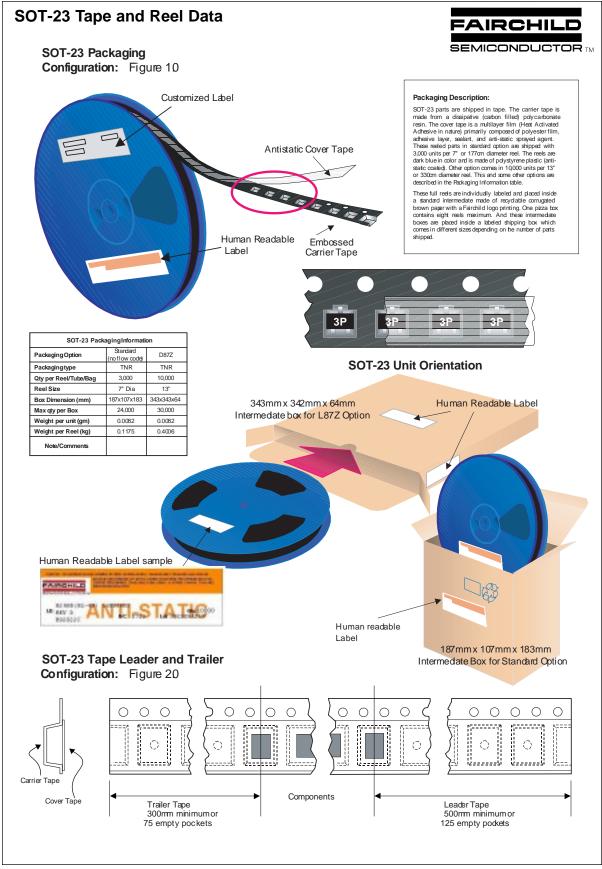
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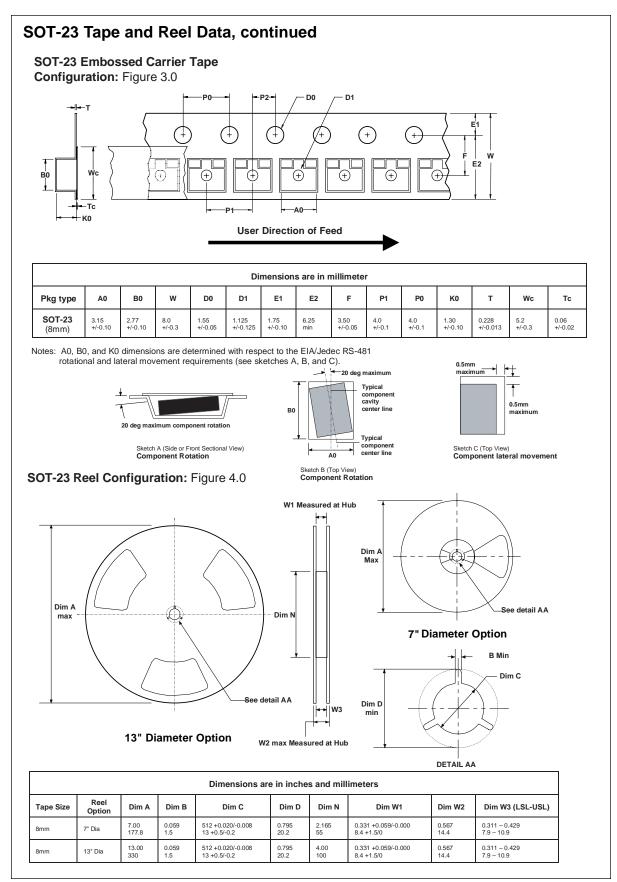
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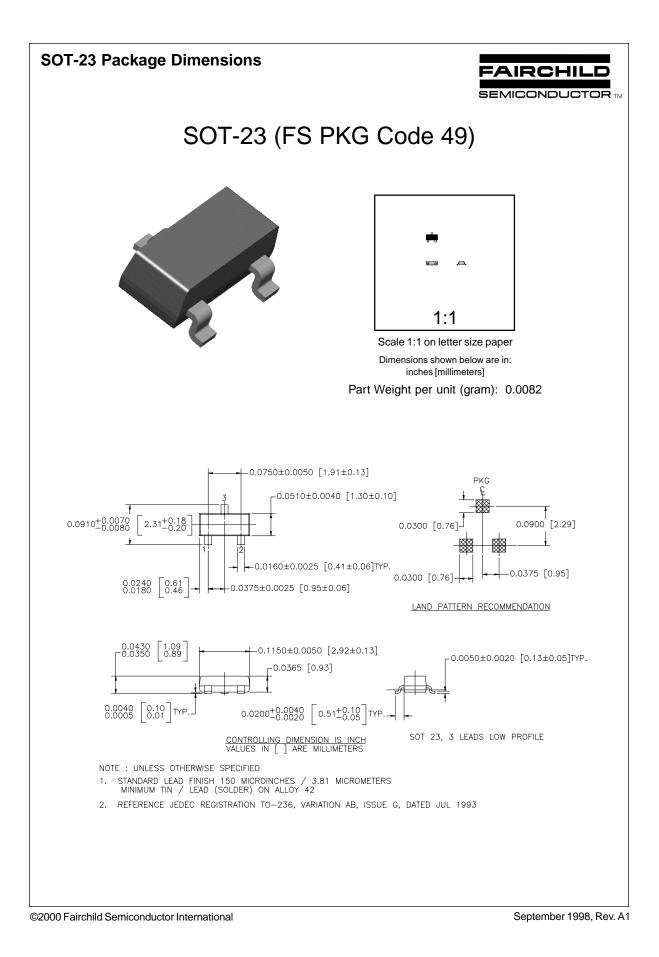


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